

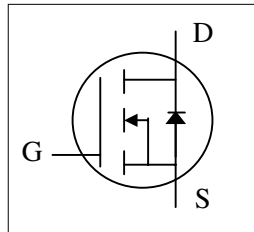
AP95T08GP

Preliminary



*N-CHANNEL ENHANCEMENT MODE
POWER MOSFET*

- ▼ Simple Drive Requirement
- ▼ Lower On-resistance
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant

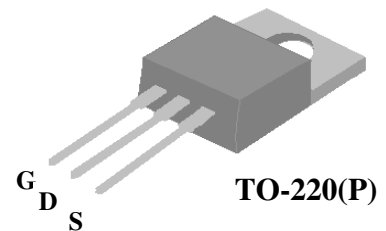


BV_{DSS}	80V
$R_{DS(ON)}$	7m Ω
I_D	80A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial power applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^3$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	70	A
I_{DM}	Pulsed Drain Current ¹	320	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	300	W
	Linear Derating Factor	2	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Thermal Resistance Junction-case	Max. 0.5	$^\circ C/W$
R_{thj-a}	Thermal Resistance Junction-ambient	Max. 62	$^\circ C/W$



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Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =1mA	80	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.06	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =60A	-	-	7	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	5	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =60A	-	56	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =80V, V _{GS} =0V	-	-	10	uA
	Drain-Source Leakage Current (T _j =150°C)	V _{DS} =64V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =40A	-	93	150	nC
Q _{gs}	Gate-Source Charge	V _{DS} =64V	-	26	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	42	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =40V	-	23	-	ns
t _r	Rise Time	I _D =40A	-	96	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	39	-	ns
t _f	Fall Time	R _D =1Ω	-	65	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	4450	7120	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	850	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	360	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =60A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time ²	I _S =40A, V _{GS} =0V	-	72	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	170	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Package limitation current is 80A, calculated continuous current based on maximum allowable junction temperature is 142A.

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

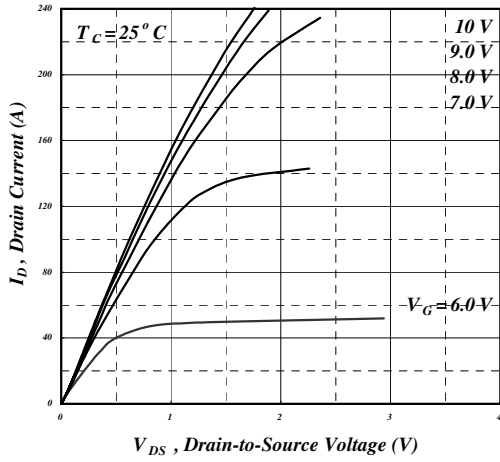


Fig 1. Typical Output Characteristics

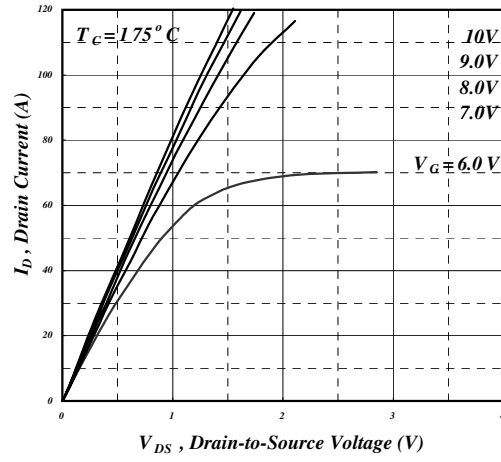


Fig 2. Typical Output Characteristics

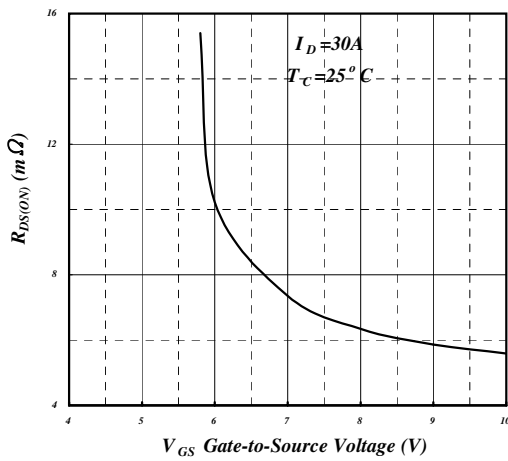


Fig 3. On-Resistance v.s. Gate Voltage

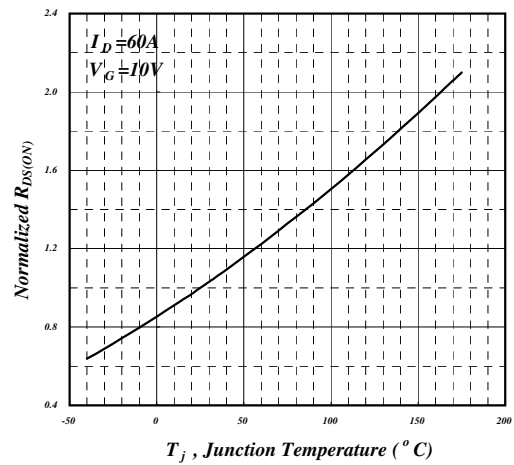


Fig 4. Normalized On-Resistance v.s. Junction Temperature

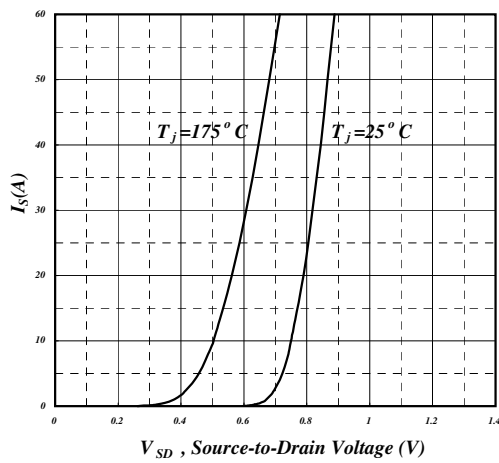


Fig 5. Forward Characteristic of Reverse Diode

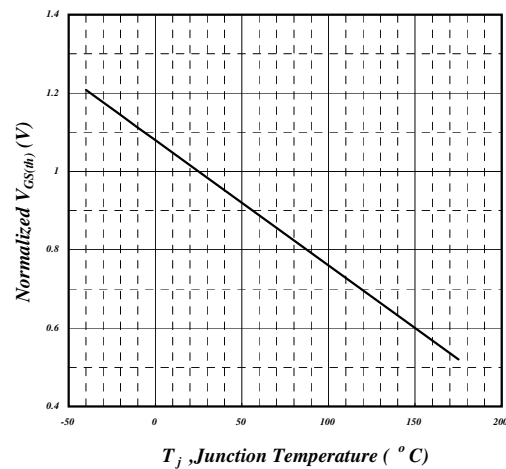


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

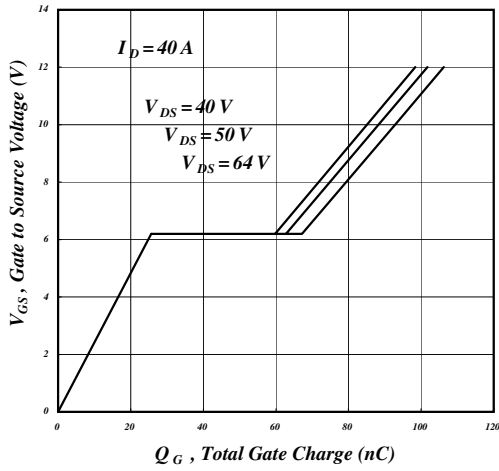


Fig 7. Gate Charge Characteristics

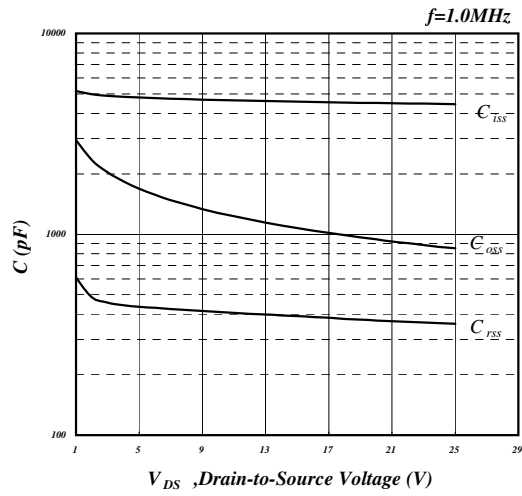


Fig 8. Typical Capacitance Characteristics

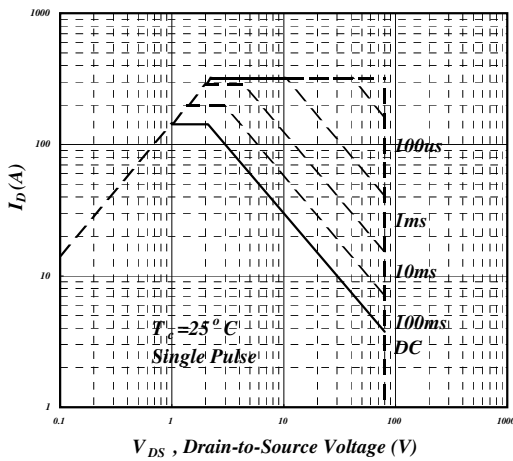


Fig 9. Maximum Safe Operating Area

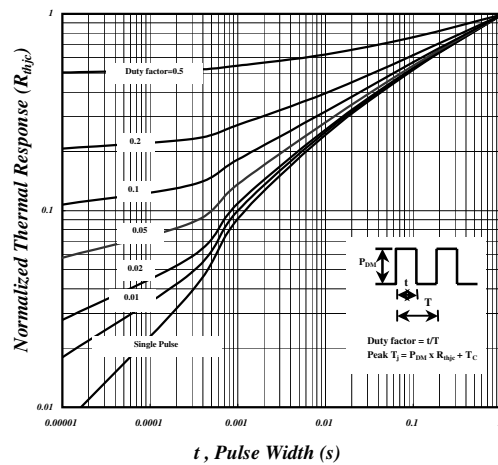


Fig 10. Effective Transient Thermal Impedance

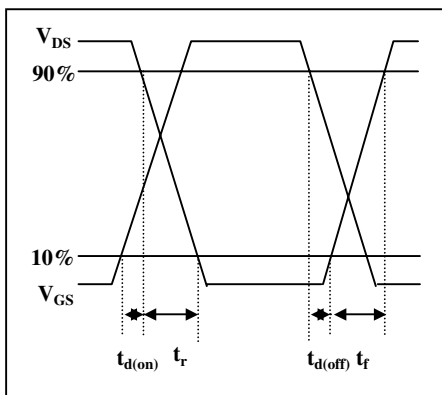


Fig 11. Switching Time Waveform

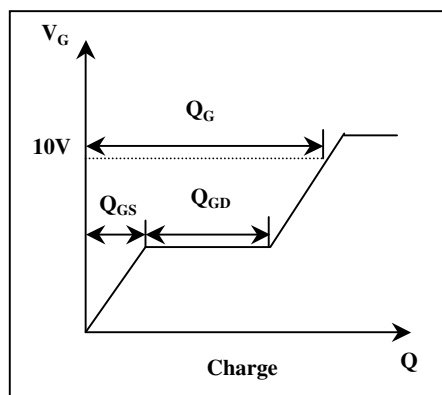


Fig 12. Gate Charge Waveform